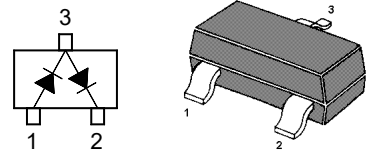


BAV99

Silicon Epitaxial Planar Switching Diode

Fast switching in thick and thin-film circuits diode



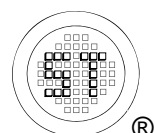
Marking Code: A7
TO-236 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

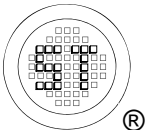
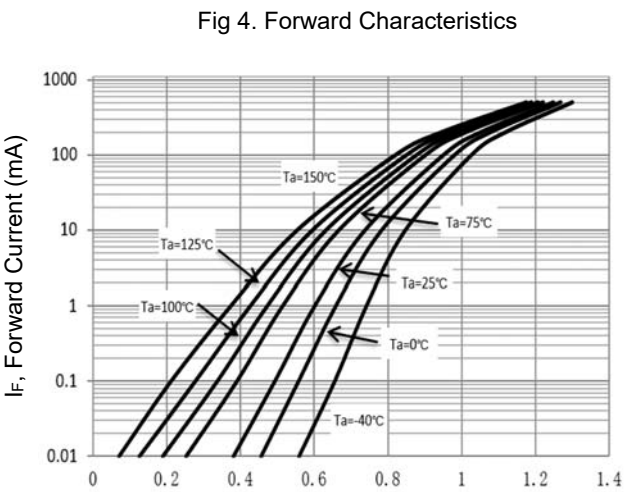
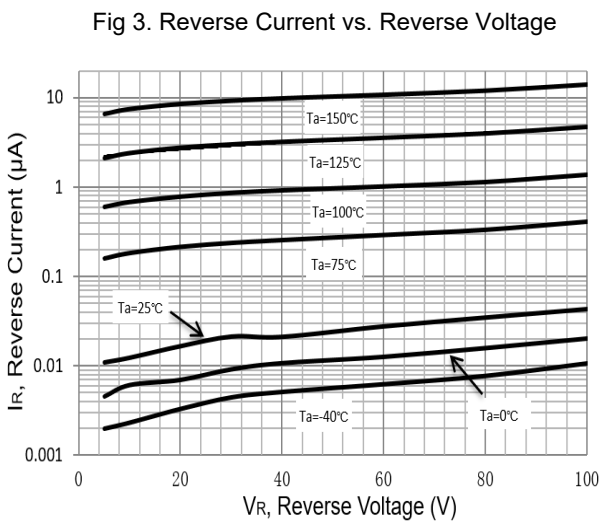
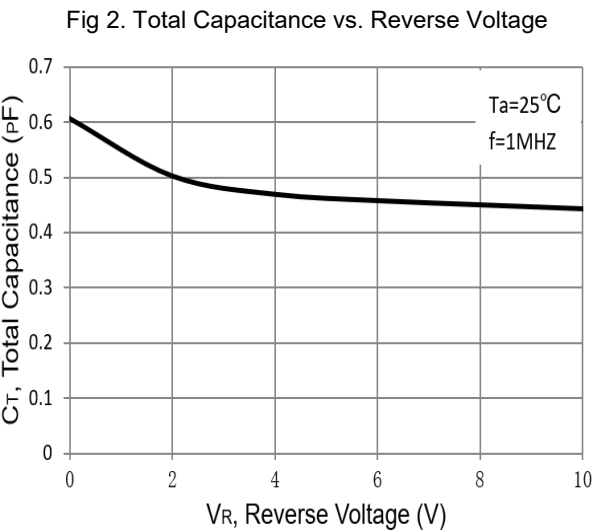
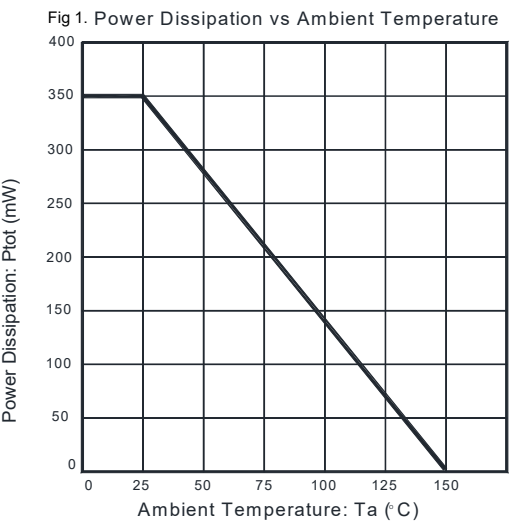
Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Continuous Reverse Voltage	V_R	100	V
Continuous Forward Current (Double Diode Loaded)	I_F	125	mA
Continuous Forward Current (Single Diode Loaded)	I_F	215	mA
Repetitive Peak Forward Current	I_{FRM}	450	mA
Non-repetitive Peak Forward Surge Current	I_{FSM}	0.5 1 4.5	A
Power Dissipation	P_{tot}	350	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 10\text{ mA}$ at $I_F = 50\text{ mA}$ at $I_F = 150\text{ mA}$	V_F	0.715 0.855 1 1.25	V
Reverse Current at $V_R = 25\text{ V}$ at $V_R = 75\text{ V}$ at $V_R = 25\text{ V}$, $T_j = 150^\circ\text{C}$ at $V_R = 75\text{ V}$, $T_j = 150^\circ\text{C}$	I_R	30 1 30 50	nA μA μA μA
Total Capacitance at $V_R = 0$, $f = 1\text{ MHz}$	C_T	1.5	pF
Reverse Recovery Time at $I_{rr} = 0.1 \times I_R$, $I_F = 10\text{ mA}$, $V_R = 6\text{ V}$, $R_L = 100\ \Omega$	t_{rr}	4	ns

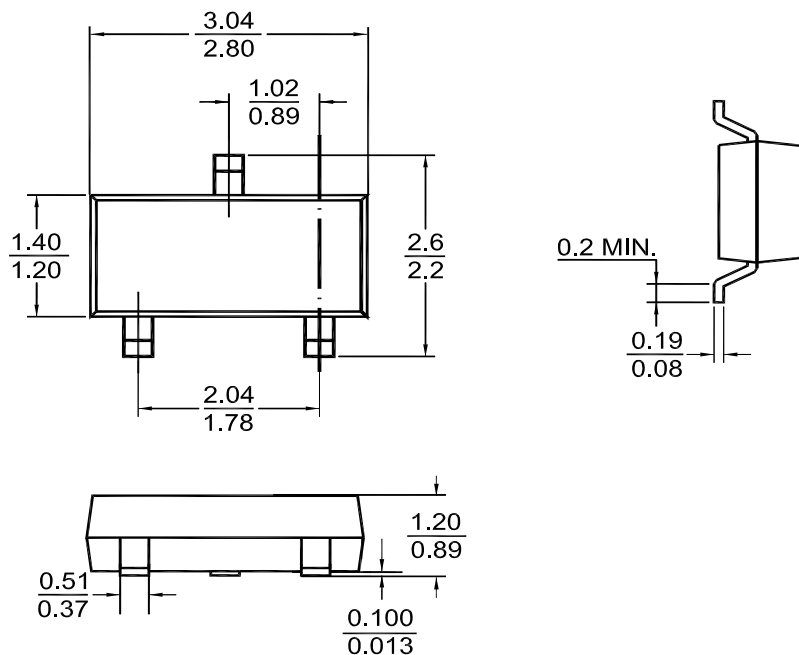


Electrical Characteristics Curves

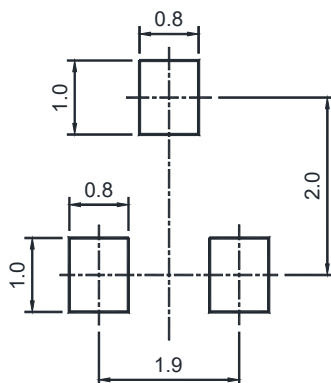


Package Outline (Dimensions in mm)

TO-236



Recommended Soldering Footprint



Packing information

Package	Tape Width (mm)	Pitch		Reel Size		Per Reel Packing Quantity
		mm	inch	mm	inch	
TO-236	8	4 ± 0.1	0.157 ± 0.004	178	7	3,000

Marking information

" A7 " = Part No.
 " YM " = Date Code Marking
 " Y " = Year
 " M " = Month
 Font type: Arial

